

Please replace the paragraph beginning at page 4, line 23, with the following replacement paragraph:

A3  
--According to another aspect of the present invention, there is provided a solid-state imaging device having a gate structure including an oxide film and a nitride film, including: upper layer films allowing ultraviolet rays having a wavelength of 400 nm or less to pass therethrough; and an organic film capable of absorbing the ultraviolet rays, the organic film being formed in such a manner as to cover a region of the gate structure including an oxide film and a nitride film, excluding a light receiving portion and a transfer portion, of the solid-state imaging device.--

Please replace the paragraph beginning at page 5, line 10, with the following replacement paragraph:

A4  
--With these configurations, since the metal made shield film or the organic film capable of absorbing ultraviolet rays is provided to cover an MONOS gate structure region, excluding a light receiving portion and a transfer portion, of the solid-state imaging device, it is possible to prevent ultraviolet rays from entering the MONOS gate structure excluding the light receiving portion and transfer portion, for example, an output gate and a reset gate. As a result, it is possible to prevent the deterioration of the solid-state imaging device and hence to improve the reliability of the solid-state imaging device.--

Please replace the paragraph beginning at page 11, line 1, with the following replacement paragraph:

A5  
--A second solid-state imaging device 2 as the second embodiment shown in FIG. 2 has the same basic configuration as that of the first solid-state imaging device 1 shown in FIGS. 1A and 1B, except that an organic film for absorbing ultraviolet rays is used in place of the metal made shield film. The organic film may be made from a colored resist. Preferably, the colored resist has an ability of absorbing 95% or more of ultraviolet rays having a wavelength of 400 nm or less. Further, the absorbance of the organic film may be determined based on a combination of a material of an organic film and a film thickness.--